Absorption Improvement and EM Spectroscopy in Photodetector based on Plasmonic Effect by Introducing Sio2 Layer and Ag Nano Particles

Sayyed Salar Hosseini¹, Omid Davarpanahi² and Hasan Rasooli³

¹ Islamic Azad University

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8 Abstract

⁹ We have a light detector structure based on plasmonic effects for maximum light absorption at ¹⁰ a wavelength of 820 nm have suggested and the two-stage absorption rate to have increased ¹¹ considerably compared to the previous ones. Firstly, by placing layers of glass between gold ¹² and the semiconductor GaAs is Grating and secondly embedding silver nanoparticles in the ¹³ metal Grating gold. With the implementation of each stage can be seen to increase light ¹⁴ absorption in the detector in this structure we proposed for the first time we've done it both ¹⁵ ways, to intensify the absorption coefficient is 25.83.

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17 Index terms— nanostructured materials, photodetectors, plasmons, metal grating, nanoparicles.

18 1 INTRODUCTION

oday, the network of data transmission Such as the fitting of Types of the high-speed chip, Internet and telephone 19 communication has created incentives to build and use light detectors. study of the structure of Light metal-20 semiconductor-metal detectors from the early 1970s began [1]. The surface plasmon resonance in the context of 21 the emergence and realization of sub-wavelength aperture to improve the absorption of light. In recent decades a 22 23 number of experimental work and theory research to study ultralight transmission through The reviews ultra-light 24 transmission by sub-wavelength aperture is done. [2] Nano grating nano-under-wavelength light creates a robust response and for potential trapping the light in the semiconductor area. Interconnect metalsemiconductor-metal 25 detector electrodes led to a significant increase in bandwidth and reduce the dark current in the detector LED 26 p-i-n structures that have the same active region, is. [3] Detectors plasmonic nanoscale response time due to the 27 distance between the electrodes is about a few tens of picoseconds to the transportation of products from the 28 metal connection is limited. In addition, reducing the distance the electrodes will lead to a reduction in the active 29 region and the decrease in sensitivity. [4] Surface plasmons, which are electromagnetic waves along a metal are 30 released. Properties of their interaction with light, causing surface polariton plasmon waves and create features 31 by which we can photonic components with dimensions much smaller than what has been achieved to build. [5] 32 study and understanding of the plasmons, are widely idea of what began in the 1950s after the article was. These 33 34 studies also cast a frequent flashpoint of the surface plasmons in thin metal Filter trick of the light scattering of 35 particles of nano metal was done in the early 1970s. Find the improved transmission of light through periodic 36 array of holes with dimensions smaller than the wavelength plasmons in metal films drew much attention. [6] 37 a) The structure design Metal-semiconductor-metal detector structure usually consists of three separate parts, including: 38

A) metal grating, b) sub-wavelength aperture and f) substrate Is as shown in Figure 1. Part A metal grating that includes a good conductor and the x axis is parallel grooves. Dimensions has been optimized light wavelength surface plasmon polariton is designed to be coupled along the axis x prompt. Surface plasmon polariton wave vector with a period ? for metal grating in Equation 1, we see that in 1991 was used by Soole. In relation (1), ? the angular frequency, ? the angle of the incoming light, c is the speed of light in vacuum and permittivity factor in the metal in the form of equation (2) is defined. In reference [1] is mentioned.? ? = ? ? ? +?? ?? (2)

? ? is the air permittivity used. Each groove surface plasmon polariton ? ??? metal grating by electric field

excitation and emission during both positive and negative x-axis location will be done. Surface plasmon polariton
 wave intensity decreases exponentially with propagation distance and depth is a factor that is proportional to

permittivity material. [7] The amplification factor of attraction for "normalized power transition metal grating

49 detector on "normalized power no = structure transition metal grating as in reference [7] are used, we define.

⁵⁰ The surface plasmon polariton by restrictions on slots (not the center) to release the sub-wavelength aperture ⁵¹ triggered a wave of surface plasmon polariton light input (which is presented in Figure (??) with ??) interference

(coupling) is.] 2] the total surface plasmon polariton increase optical transmission through subwavelength aperture
 is. In fact, metal grating as collector or lens focused wave in the resonant frequency of the acts. Highly dependent

increase in light transmission parameters such as frequency grating ? ? and thick metal grating is ? ð ??". [7]
Coupled surface plasmon polariton wave ? ??? of the incoming wave ? ? hybrid transmission ? 12 and it've shown

in Figure (2). Using semi-analytical calculation Fabry-Perot [8] and formalism expansion mode [2] Green tensor analysis [9] In reference [7] is calculated; When the subwavelength aperture width x_d is much smaller than the wavelength of emission ? 0, increase light transmission and improve absorption in semiconductors absorb

light transmission caused by metal grating can be achieved. A more accurate model improved light transmission
through sub-wavelength aperture as well as by Sturman and et [10] described. Modify the parameters of (1)
changes in the semiconductor light transmission is desired wavelength. So we improved the best parameters [7]

62 use.

⁶³ 2 b) The simulation desired model

In this article we improve absorption in three stages as follows absorbance at a wavelength of 820 nm have the amplification factor, we speak to all three structures. Finite difference time domain simulation models expressed are using.

We design gold metal grating (Au) and the substrate of gallium arsenide (GaAs) consider. Gold permittivity rate? ? of Drude-Lorentz model worked in the reference [11] and the coefficient of permittivity substrate (gallium arsenide) ?_sub real value was assumed to be 12.25. The imaginary part for infrared wavelengths were ignored. [12] Fig. 3-A The idea of putting layers of glass (SiO2) between gold grating and substrate gallium arsenide 1. plasmonic optical detector structure with gold grating and gallium arsenide substrate.

72 2. plasmonic optical detector structure with gold grating and substrate layers of glass between gold grating and gallium arsenide substrate (under sub-wavelength aperture) of the E-plain Tee is a split in the microwave, is 73 74 used [13] The detector is also used by Jamalpur et al. was. [14] performance glass substrate which is an insulator 75 for the rejection of electron-hole pairs in the semiconductor to metallic connection. To sum carriers on both 76 sides of the gold structure can be used vertically. In this structure, the absorption rate was 0.24. Figure 4 shows a structure in the form of (4-B) absorption at a wavelength of 820 nm curve we see. Our silver nanoparticles 77 under sub-wavelength aperture (in place of glass layer) placed. This is similar to gallium arsenide substrate 78 and intermediate layer of germanium. [15] Due to the high refractive index semiconductor base frequency must 79 be chosen too small metallic nanoparticles. It features some difficult and sensitive process with a common 80 manufacturing techniques. In this structure, the absorption rate was 0.31. Figure 5 shows a structure in the 81 form of (5-b) absorption at a wavelength of 820 nm curve we see. In this paper, results of the three proposed 82 structure your previous jobs on the graph (1) We compare the amplification factor of attraction for "normalized 83 84 power transition detector with metal grating" on "normalized power without transition metal grating " in [7] is 85 used to optimize and use our sub-contractor relations.??? = ? ???, ∂ ??" ? ??? (3)

Explaining the relation (??) is as follows: Absorption Enhancement Factor as the ratio of: the normalized power transmittance of the metal-grating MSM photo detector to the normalized power transmittance of an MSM photo detector structure without a metal grating.

This relationship is expressed for the results of three structures and substrate in the denominator we can use as a reference gallium arsenide. Normalized power transmission substrate gallium arsenide (without metal grating) in the form (6) is shown at a wavelength of 820 nm is equal to 0.012. we have established that by performing

92 finite element EM computation to the following expression, the absorption QE, labeled as ?, of any detector 93 geometry can be predicted [16]:? = ?? ?? 0 2 ? |? ? (? ?)| 2 ? 3 ? ? (4)

where n is the material refractive index of the detector material, ? is the absorption coefficient for vertically 94 95 polarized light, A is the detector area, E0 is the incident electric field from the air, V is the detector active 96 volume, Ez is the self-consistent vertical electric field. Equation (??) states that QE can be calculated from the 97 volume integral of |Ez |2 in the presence of a finite ?. Since E0 and Ez are linearly proportional to each other, 98 E0 can be set arbitrarily, and the only input parameter in (1) is the wavelength-dependent ?(?), which can be calculated based on the material layer structure [17]. For a known ?(?), there will be no more free parameters, 99 and the value of ?(?) is uniquely and unambiguously determined. To solve Ez numerically, we use a commercial 100 finite element solver. In addition to ?, we also define another quantity, the external QE or ?ext , which is QE \times 101 pixel area fill factor (?A/Apitch). (5) 102

103 Which represents an increase absorption due to grating adjusting parameters compared with similar structure.

Results of the 2-3 structure plasmonic optical detector with gallium arsenide layers of glass between Gold grating 104 and substrate in equation (2), we have: $??? = 0.243 \ 0.012 = 20.25(6)$ 105

Results 3-3 of plasmonic optical detector structure with silver nanoparticles on glass substrates, gallium 106 arsenide between Gold grating and infrastructure in equation (2) we have: $??? = 0.31 \ 0.012 = 25.83(7)$ 107 II. 108

3 Simulation Setup 109

The 3D -plasmonic optical detector structure shown in Fig. 5(a) was simulated using the FDTD software package 110 developed by Lumerical. For the FDTD simulation, we used a mesh size 10nm. This high resolution sampling 111 yielded convergent solutions at reasonable computation times. A periodic boundary condition was assumed along 112 the y-direction for an incident light wave propagated along the normal direction. perfectly matched layer (PML) 113 boundary III. 114

Conclusion 4 115

In this article we construct the optical detection based on plasmonic effects by improving the detection parameters 116 for maximum light absorption at a wavelength of 820 nm have suggested. We improved amplification factor of 117 attraction even for the initial state, including gold and base gallium arsenide grating was obtained as a result of 118 adjusting parameters grating compared with a similar structure and was 14 times. The coefficient of resonant 119 absorption by adding layers of glass between gold grating and base the amount of gallium arsenide 20.25 for the 120 glass came up with. Then proceeded to put silver nanoparticles on glass substrates that absorb amplification 121 factor increased to 25.83. Compared with previous work Jamalpur and colleagues [14] in 2015 which attracted 122 about 15 have reached the amplification factor, we have increased every neighborhood we have our final difference 123 1 2 3





Figure 1: Fig. 1:

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³. plasmonic optical detector structure with silver nanoparticles on glass substrates, between gold grating and gallium arsenide substrate



Figure 2:



Figure 3: Fig. 2 :



Figure 4:



Figure 5: Fig. 3 -



Figure 6: Fig. 4 -



Figure 7: Fig. 5 -



Figure 8: Fig. 5 (



Figure 9: Fig. 6 :



Figure 10: Fig. 7 -



Figure 11: F

4 CONCLUSION

- 125 [Marcuitz ()] , N Marcuitz . 1950. New York Dover Publications. p. .
- 126 [Courtney ()], W E Courtney. IEEE Trans. Microw. Theory Tech 1977. 25.
- 127 [Rakic´ et al. ()] , D Rakic´ , A B Djuri?ic´ , J M Elazar , M L Majewski . Appl. Opt 1998. 37 p. 5271.
- 128 [Sturman et al. ()], B Sturman, E Podivilov, M Gorkunov. Phys. Rev. B 2008. 77 p. 75106.
- [White et al. ()], Justin S White, Georgios Veronis, Zongfu Yu, Edward S Barnard, Anu Chandran, Shanhui
 Fan, Mark L Brongersma. Opt. Lett 2009. 34 (5) p. 686.
- IJamalpoor et al. (2015)] 'A new approach for absorption enhancement in plasmonic photodetectors'. Kamal
 Jamalpoor, Abbas Zarifkar, Abbas Alighanbari. The 21st Iranian Conference on Optics & Photonics & 7th
 Iranian Conference On Photonics Engineering 13-15, January 2015. p. . Shahid Beheshti University
- 134 [Tan et al. ()] 'Absorption enhancement of 980 nm MSM photodetector with a plasmonic grating structure'. C
- L Tan , V V Lysak , K Alameh , Y T Lee . Optics Communications Elsevier 2009. 283 (9) p. .
- [Ebbesen et al. ()] 'Extraordinary optical transmission through sub-wavelength hole arrays'. T W Ebbesen , H J
 Lezec , H F Ghaemi , T Thio , P A Wolff . Nature 1998. 391 p. .
- [Eker et al. (2010)] 'High conversion efficiency InP/InGaAs strained quantum well infrared photodetector focal
 plane array with 9.7 ?m cut-off for high-speed thermal imaging'. S U Eker , Y Arslan , A E Onuk , C Besikci *IEEE J. Quantum Electron* Feb. 2010. 46 (2) p. .
- [Soole and Schumacher ()] 'InGaAs metalsemiconductor-metal photodetectors for long wavelength optical communication'. J B D Soole , H Schumacher . *IEEE J. Quantum Electronics* 1991. 27 (3) p. .
- [Hecht et al. ()] 'Local excitation, scattering, and interference of surface plasmons'. B Hecht , H Bielefeldt , L
 Novotny , Y Inouye , D W Pohl . *Physical Review Letters* 1996. 77 p. .
- [Ito and Wada (1986)] 'Low dark current GaAs metalsemiconductormetal (MSM) photodiodes using WSi
 contacts'. M Ito , O Wada . *IEEE J. Quantum Electron* Jul. 1986. 22 (7) p. .
- [García-Vidal et al. ()] Multiple Paths to Enhance Optical Transmission through a Single Subwavelength Slit, F
 J García-Vidal, H J Lezec, T W Ebbesen, L Martín-Moreno. 2003. 90 p. 213901. (physical review letters)
- 149 [Chee Leong Tan et al. (2013)] 'Optical absorption enhancement of hybrid-plasmonic-based
- 150 metalsemiconductor-metal photodetector incorporating metal nanogratings and embedded metal
- nanoparticles'. Ayman Chee Leong Tan , Kamal Karar , Yong Tak Alameh , Lee . OPTICS EXPRESS
 January 2013. 28 (2) p. 1713. (OSA)
- [Hetterich et al. ()] 'Optimized design of plasmonic MSM photodetector'. J Hetterich , G Bastian , N A Gippius
 , S G Tikhodeev , G Von Plessen , U Lemmer . *IEEE J. Quantum Electronics* 2007. 40 (10) p. .
- [Wu et al. ()] 'Plasmonic enhanced quantum well infrared photodetector with high detectivity'. W Wu , A
 Bonakdar , Mosheni . Appl. Phys. Lett 2010. 96 p. .
- [Weiner ()] The physics of light transmission through subwavelength apertures and aperture arrays, J Weiner .
 2009. 72. (reports on progress in physics)